# SILICON PROCESSING FOR THE VLSI ERA

### **VOLUME 1:**

### PROCESS TECHNOLOGY

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LATTICE PRESS

Sunset Beach, California



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Published by:

Lattice Press

Post Office Box 340 Sunset Beach, California 90742, U.S.A.

Cover design by Roy Montibon and Donald Strout, Visionary Art Resources, Inc., Santa Ana, CA.

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Library of Congress Cataloging in Publication Data Wolf, Stanley and Tauber, Richard N.

Silicon Processing for the VLSI Era Volume 1: Process Technology

Includes Index

 Integrated circuits-Very large scale integration.
 Silicon. I. Title

86-081923

ISBN 0-961672-3-7

9 8 7 6 5 4

PRINTED IN THE UNITED STATES OF AMERICA



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